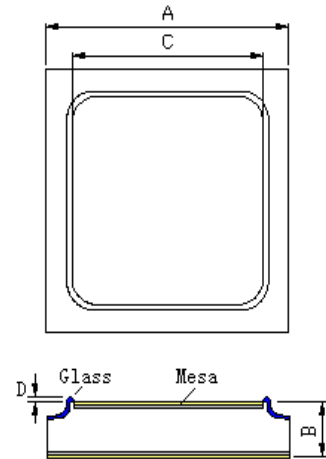


## Features

- Glass passivated chip
- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability
- Surface Metalization: Ni(0.6~1um)/Au(0.05um)
- Compatible with soldering
- Operating Junction temperature range :-55 ~ +150°C
- Standard Recovery Rectifier



## Process Details

Chip Part No.	Chip size	PDPW (pcs/4"wafer)	Size (mil)			
			A (+1/-2)	B (±1)	C (±2)	D (±)
GDGS41A-M	41*41mil	6,700	41	10	23	1
GDGS45A-M	45*45mil	5,299	45	10	26	1
GDGS50A-M	50*50mil	4,469	50	10	31	1
GDGS56A-M	56*56mil	3,685	56	10	36	1
GDGS60A-M	60*60mil	3,011	60	10	37	1
GDGS72A-M	72*72mil	2,045	72	10	46	1
GDGS84A-M	84*84mil	1,469	84	10	58	1
GDGS88A-M	88*88mil	1,313	88	10	62	1
GDGS95A-M	95*95mil	1,153	95	10	69	1
GDGS110A-M	110*110mil	853	110	10	84	1
GDGS130A-M	130*130mil	613	130	10	104	1
GDGS140A-M	140*140mil	521	140	10	114	1
GDGS160A-M	160*160mil	406	160	10	131	1
GDGS180A-M	180*180mil	316	180	10	151	1
GDGS200A-M	200*200mil	256	200	10	194	1

## Maximum Ratings

(TA = 25 °C unless otherwise noted)

Parameter	Symbol	VALUE							UNIT
		A	B	D	G	J	K	M	
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	See Next Table							A
Maximum instantaneous forward voltage at IF	$V_F$	See Next Table							V
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	$I_{FSM}$	See Next Table							A

## Representative Parameter

Chip size/mil	$I_F(A)$	$V_F(V)@I_F$	$V_{BL}(V)@I_1=10\mu A$	$I_R(\mu A)@V_R$	$I_{FSM}(A)$
41	1	1	50~1000	1	25
45	1	1	50~1000	1	30
50	1	1	50~1000	1	30
56	1.5	1	50~1000	1	50
60	1.5	1	50~1000	1	50
72	2	1	50~1000	1	60
84	3 or 4	1	50~1000	1	100
88	4 or 5	1	50~1000	1	120
95	5	1	50~1000	1	150
110	7.5	1	50~1000	1	200
130	10	1	50~1000	1	270
140	12.5	1	50~1000	1	300
160	17.5	1	50~1000	1	350
180	20	1	50~1000	1	400
200	25	1	50~1000	1	450